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TRANSMITTAL FORM (to be used for all correspondence after initial f	Applicati Filing Da First Nar Art Unit Examine	to respond to a collection of on Number 10 Ite A ned Inventor G Ite Collection of the collection of	PTO/SB/21 (03-03) Approved for use through 04/30/2003. OMB 0651-0031 and Trademark Office; U.S. DEPARTMENT OF COMMERCE of information unless it displays a valid OMB control number. 0/636,038 August 6, 2003 Gurtej Sandhu 8812 Inkonwn
Fee Transmittal Form Fee Attached Amendment/Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53	Petition Petition to C Provisional / Power of Att	onvert to a Application orney, Revocation orrespondence Address claimer Refund of CD(s)	After Allowance Communication to a Technology Center (TC) Appeal Communication to Board of Appeals and Interferences Appeal Communication to TC (Appeal Notice, Brief, Reply Brief) Proprietary Information
Firm or Wells St. John, P.S. Signature Date Mark S. Matkin, Reg No. 3: Wells St. John, P.S. CE	2,268 RTIFICATE OF Simile transmitted to the	TRANSMISSION/M USPTO or deposited with thington, DC 20231 on this of	TAILING the United States Postal Service with sufficient postage as
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This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, preparing upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No	10/636,038
Filing Date	
Inventor	Gurtej Sandhu
Assignee	Micron Technology, Inc.
Group Art Unit	2812
Examiner	Unknown
Attorney's Docket No	MI22-2194
Title: Methods of Forming Material on a Substrate an	id a Method of Forming a
Field Effect Transistor Gate Oxide on a Substrate	

INFORMATION DISCLOSURE STATEMENT

References – See Attached Form PTO-1449

To:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Ey372467864

From:

(Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

Dear Sir:

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449 and copies of which are attached.

This Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing of a first Office Action, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Information Disclosure Statement, please charge the fee specified under 37 C.F.R. §1.17(p) to Deposit Account No.

23-0925. Please credit Deposit Account No. 23-0925 with any overpayment of the above fee.

Citations of these references are respectfully requested.

Respectfully submitted,

Dated: //-

Namb C

Reg. No. 32,268

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO.
MI22-2194	10/636,038
APPLICANT Gurtej Sandhu	
FILING DATE	GROUP
August 6, 2003	2812

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	AA	6,495,436	12/17/2002	Ahn et al.			
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	AL						
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	AM						Yes No
	AN						
	ΑO						
	AP						
	ΛQ						
•			OTHER REFERENC	EES (including Author, Title, Date, Pertinent Pages, Etc.)			
	AR	"Surface preparation pp. 326-331.	and post thermal treatmen	nt effects on interface properties of thin $\Lambda L_2 O_3$ films depos	ited by ALD ;" Chan	g et al.; Microele	etronic Engineering 72, 2004;
	AS	"Effect Purge time 2004; pp. 2-8.	on the properties of HfO ₂ f	ilms prepared by atomic layer deposition;" Kawahara et al.: l	IELEEJ Transactions	s on Electronics; \	Vol. E87-C, No. 1; January
	АΤ			etries: a comparison of ALCVD and MOCVD as deposition to oc. Symposium Proceedings Vol. 765); April 22-24, 2003; 47		x et al.; CMOS F	ront-End materials and
EXAMINER		DATE CONSIDER	ED				

Form PTO-1449

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	AN		Date	Country	Class	Subclass		Ne
	AN AO		Date	Country	Class	Subclass		Ne
	AN AO AP		Date	Country	Class	Subclass		No
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	AN AO AP AQ AR	"Effect of Hf sour Applied Physics, Vo	OTHER REFERENCES res, oxidizing agents, and NH ₂ /A sl. 43, No. 7A: July 2004; pp. 41.	(including Author, Title, Date, Pertinent P. r plasma on the properties of HfAlO, films p 29-4134.	iges, Etc.)	on;' Kawahara et	Yes	nal of

this form with next communication to applicant.